

HiPerFET™ Power MOSFETs IXFR 180N085 ISOPLUS247™ (Electrically Isolated Back Surface)

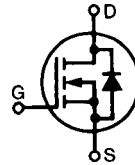
$$V_{DSS} = 85 \text{ V}$$

$$I_{D25} = 180 \text{ A}$$

$$R_{DS(on)} = 7 \text{ m}\Omega$$

$$t_{rr} \leq 250 \text{ ns}$$

Single MOSFET Die

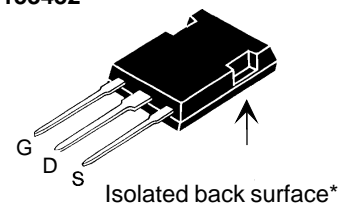


Preliminary data sheet

| Symbol | Test Conditions | Maximum Ratings | |
|---------------|---|-----------------|------------------|
| V_{DSS} | $T_J = 25^\circ\text{C}$ to 150°C | 85 | V |
| V_{DGR} | $T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1 \text{ M}\Omega$ | 85 | V |
| V_{GS} | Continuous | ± 20 | V |
| V_{GSM} | Transient | ± 30 | V |
| I_{D25} | $T_C = 25^\circ\text{C}$ (MOSFET chip capability) | 180 | A |
| $I_{D(RMS)}$ | External lead current limit | 76 | A |
| I_{DM} | $T_C = 25^\circ\text{C}$, Note 1 | 720 | A |
| I_{AR} | $T_C = 25^\circ\text{C}$ | 180 | A |
| E_{AR} | $T_C = 25^\circ\text{C}$ | 60 | mJ |
| E_{AS} | $T_C = 25^\circ\text{C}$ | 3 | J |
| dv/dt | $I_S \leq I_{DM}$, $di/dt \leq 100 \text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$ $T_J \leq 150^\circ\text{C}$, $R_G = 2 \Omega$ | 5 | V/ns |
| P_D | $T_C = 25^\circ\text{C}$ | 400 | W |
| T_J | | -55 ... +150 | $^\circ\text{C}$ |
| T_{JM} | | 150 | $^\circ\text{C}$ |
| T_{stg} | | -55 ... +150 | $^\circ\text{C}$ |
| T_L | 1.6 mm (0.063 in.) from case for 10 s | 300 | $^\circ\text{C}$ |
| V_{ISOL} | 50/60 Hz, RMS $t = 1 \text{ min}$ | 2500 | V~ |
| Weight | | 5 | g |

ISOPLUS 247™

E153432



G = Gate D = Drain
S = Source

* Patent pending

Features

- Silicon chip on Direct-Copper-Bond substrate
- High power dissipation
- Isolated mounting surface
- 2500V electrical isolation
- Low drain to tab capacitance (<25pF)
- Low $R_{DS(on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Fast intrinsic Rectifier

Applications

- DC-DC converters
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- AC motor control

Advantages

- Easy assembly
- Space savings
- High power density

| Symbol | Test Conditions | Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified) | | |
|--------------|---|---|------|---------------------------|
| | | min. | typ. | max. |
| V_{DSS} | $V_{GS} = 0 \text{ V}$, $I_D = 3 \text{ mA}$ | 85 | | V |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D = 8 \text{ mA}$ | 2.0 | 4.0 | V |
| I_{GSS} | $V_{GS} = \pm 20 \text{ V}$, $V_{DS} = 0$ | | | $\pm 100 \text{ nA}$ |
| I_{DS} | $V_{DS} = V_{DSS}$, $V_{GS} = 0 \text{ V}$ | | | 100 μA 2 mA |
| $R_{DS(on)}$ | $V_{GS} = 10 \text{ V}$, $I_D = 0.5 I_{D25}$ Note 1 | | | 7 m Ω |

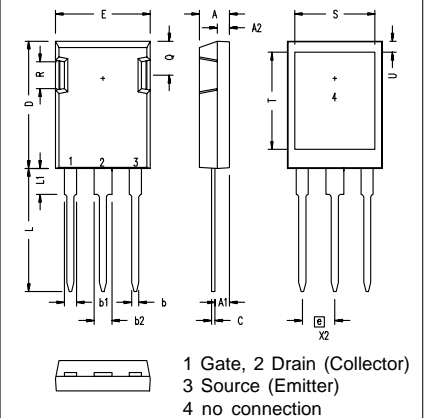
| Symbol | Test Conditions | Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified) | | |
|--------------|---|---|------|------|
| | | min. | typ. | max. |
| g_{fs} | $V_{DS} = 10\text{ V}; I_D = 60\text{ A}$ Note 2 | 55 | 90 | S |
| C_{iss} | $V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$ | | 9100 | pF |
| C_{oss} | | | 4000 | pF |
| C_{rss} | | | 2000 | pF |
| $t_{d(on)}$ | $V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 I_{D25}$ $R_G = 1\ \Omega$ (External) | | 65 | ns |
| t_r | | | 90 | ns |
| $t_{d(off)}$ | | | 140 | ns |
| t_f | | | 55 | ns |
| $Q_{g(on)}$ | $V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 I_{D25}$ | | 320 | nC |
| Q_{gs} | | | 65 | nC |
| Q_{gd} | | | 170 | nC |
| R_{thJC} | | | 0.30 | K/W |
| R_{thCK} | | 0.15 | | K/W |

Source-Drain Diode

| Symbol | Test Conditions | Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified) | | |
|----------|---|---|------|---------------|
| | | min. | typ. | max. |
| I_S | $V_{GS} = 0\text{ V}$ | | | 180 A |
| I_{SM} | Repetitive; pulse width limited by T_{JM} | | | 720 A |
| V_{SD} | $I_F = 100\text{ A}, V_{GS} = 0\text{ V}, \text{Note 1}$ | | | 1.3 V |
| t_{rr} | $I_F = 50\text{ A}, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 50\text{ V}$ | | | 250 ns |
| Q_{RM} | | | 1.2 | μC |
| I_{RM} | | | 10 | A |

Note: 1. Pulse width limited by T_{JM}
2. Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$

ISOPLUS 247 (IXFR) OUTLINE



| Dim. | Millimeter | | Inches | |
|----------------|------------|-------|----------|------|
| | Min. | Max. | Min. | Max. |
| A | 4.83 | 5.21 | .190 | .205 |
| A ₁ | 2.29 | 2.54 | .090 | .100 |
| A ₂ | 1.91 | 2.16 | .075 | .085 |
| b | 1.14 | 1.40 | .045 | .055 |
| b ₁ | 1.91 | 2.13 | .075 | .084 |
| b ₂ | 2.92 | 3.12 | .115 | .123 |
| C | 0.61 | 0.80 | .024 | .031 |
| D | 20.80 | 21.34 | .819 | .840 |
| E | 15.75 | 16.13 | .620 | .635 |
| e | 5.45 BSC | | .215 BSC | |
| L | 19.81 | 20.32 | .780 | .800 |
| L1 | 3.81 | 4.32 | .150 | .170 |
| Q | 5.59 | 6.20 | .220 | .244 |
| R | 4.32 | 4.83 | .170 | .190 |
| S | 13.21 | 13.72 | .520 | .540 |
| T | 15.75 | 16.26 | .620 | .640 |
| U | 1.65 | 3.03 | .065 | .080 |



LittleDiode supplies new, hard to find or obsolete electronic components and semiconductors all over the world.

With over two million different components listed you are sure to find the part you need.

Feel free to visit us today at our online store:

LittleDiode.com

Looking forward to providing you with the best possible service.